

# **isc** Silicon NPN Darlington Power Transistor

## **TIP131**

### DESCRIPTION

- High DC Current Gain-
- : h<sub>FE</sub> = 1000(Min)@ I<sub>C</sub>= 4A
- Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub> = 80V(Min)
- Low Collector-Emitter Saturation Voltage-: V<sub>CE(sat)</sub> = 2.0V(Max)@ I<sub>C</sub>= 4A
- Complement to Type TIP136
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

• Designed for general-purpose amplifier and low-speed switching applications

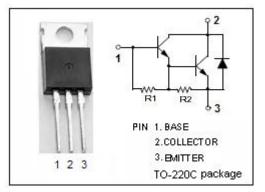
## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

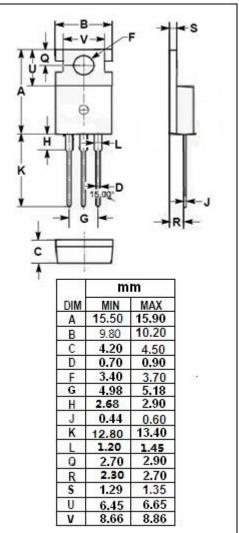
SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>CBO</sub>	Collector-Base Voltage	80	V			
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V			
V <sub>EBO</sub>	Emitter-Base Voltage	5	V			
Ic	Collector Current-Continuous	8	А			
Ісм	Collector Current-Peak	12	А			
I <sub>B</sub>	Base Current- Continuous	0.3	А			
Pc	Collector Power Dissipation @Tc=25°C	70				
	Collector Power Dissipation @Ta=25℃	2	W			
Tj	Junction Temperature 150		°C			
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C			

#### **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.785	°C/W
Rth j-a	Thermal Resistance, Junction to Ambient	63.5	°C/W

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isc website: <u>www.iscsemi.com</u>



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### **ELECTRICAL CHARACTERISTICS**

 $T_c=25^{\circ}C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA, I <sub>B</sub> = 0	80		V
VCE(sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 16mA		2.0	V
VCE(sat)-2	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A, I <sub>B</sub> = 30mA		3.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 4A; V <sub>CE</sub> = 4V		2.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 80V, I <sub>E</sub> = 0		0.2	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 40V, I <sub>B</sub> = 0		0.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		5	mA
h <sub>FE-1</sub>	DC Current Gain	Ic= 1A; V <sub>CE</sub> = 4V	500		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 4V	1000	15000	

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